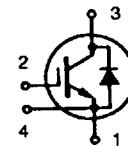


IXYS

## IGBT with Diode

IXSN55N120U1

High Short Circuit SOA Capability

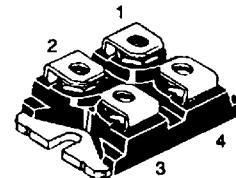
 $I_{C25} = 83 \text{ A}$   
 $V_{CES} = 1200 \text{ V}$   
 $V_{CE(sat)} = 3.5 \text{ V}$ 


Preliminary data (09/93)

Symbol	Test Conditions	Maximum Ratings		
$V_{CES}$	$T_J = 25^\circ\text{C} \text{ to } 150^\circ\text{C}$	1200	V	
$V_{GCR}$	$T_J = 25^\circ\text{C} \text{ to } 150^\circ\text{C}; R_{GE} = 1 \text{ M}\Omega$	1200	V	
$V_{GES}$	Continuous	$\pm 20$	V	
$V_{GEM}$	Transient	$\pm 30$	V	
$I_{C25}$	$T_c = 25^\circ\text{C}$	83	A	
$I_{C80}$	$T_c = 90^\circ\text{C}$	55	A	
$I_{CM}$	$T_c = 25^\circ\text{C}, t_p = 1 \text{ ms}$	110	A	
$t_{sc}$ (SCSOA)	$V_{GE} = 15 \text{ V}, V_{CE} = 0.6 \cdot V_{CES}, T_J = 125^\circ\text{C}$ $R_G = 11 \Omega$ , non repetitive	10	$\mu\text{s}$	
RBSOA	$V_{GE} = 15 \text{ V}, T_J = 125^\circ\text{C}, R_G = 11 \Omega$ Clamped inductive load, $L = 30 \mu\text{H}$	$I_{CM} = 110$ @ 0.8 $V_{CES}$	A	
$P_c$	$T_c = 25^\circ\text{C}$	403	W	
$T_J$		-40 ... +150	$^\circ\text{C}$	
$T_{JM}$		150	$^\circ\text{C}$	
$T_{sg}$		-40 ... +150	$^\circ\text{C}$	
$V_{ISOL}$	50/60 Hz $I_{ISOL} \leq 1 \text{ mA}$	$t = 1 \text{ min}$ $t = 1 \text{ s}$	2500 3000	V~ V~
$M_d$	Mounting torque (M4) Terminal connection torque (M4)		1.5/13 Nm/lb.in. 1.5/13 Nm/lb.in.	
Weight		30	g	

Symbol	Test Conditions	Characteristic Values		
		( $T_J = 25^\circ\text{C}$ , unless otherwise specified)	min.	typ.
$V_{CES}$	$I_c = 5 \text{ mA}, V_{GE} = 0 \text{ V}$	1200		V
$V_{GEM}$	$I_c = 20 \text{ mA}, V_{CE} = V_{GE}$	5		V
$I_{CES}$	$V_{CE} = 0.8 \cdot V_{CES}$ $V_{GE} = 0 \text{ V}$	$T_J = 25^\circ\text{C}$ $T_J = 125^\circ\text{C}$		750 $\mu\text{A}$ 18 mA
$I_{GES}$	$V_{CE} = 0 \text{ V}, V_{GE} = \pm 20 \text{ V}$			$\pm 500$ nA

miniBLOC, SOT-227 B



1 = Emitter, 2 = Gate  
3 = Collector, 4 = Kelvin Emitter

## Features

- International standard package miniBLOC (ISOTOP compatible)
- Isolation voltage 3000 V~
- UL registered (E 72873 M)
- 2nd generation HDMOS™ process
  - for high short circuit SOA
- Low  $V_{CE(sat)}$ 
  - for minimum on-state conduction losses
- MOS Gate turn-on
  - drive simplicity
- Fast Recovery Epitaxial Diode (FRED)
  - short  $t_{rr}$  and low  $I_{RM}$
- Low collector-to-case capacitance
  - reduced RFI
- Low package inductance
  - easy to drive and to protect

## Applications

- AC motor speed control
- DC servo and robot drives
- Uninterruptible power systems (UPS)
- Switched-mode and resonant-mode power supplies
- DC choppers

## Advantages

- Easy to mount with 2 screws
- Space savings
- High power density

## IXSN55N120U1

Symbol	Test Conditions	Characteristic Values			
		( $T_J = 25^\circ\text{C}$ , unless otherwise specified)	min.	typ.	max.
$V_{CE(on)}$	$I_C = I_{C90}, V_{GE} = 15 \text{ V}$			3.5	V
$g_m$	$I_C = I_{C90}, V_{CE} = 20 \text{ V}$ , Pulse test, $t \leq 300 \mu\text{s}$ , duty cycle $\delta \leq 2\%$	10	20		S
$I_{C(on)}$	$V_{GE} = 15 \text{ V}$		300		A
$C_{iss}$	$V_{CE} = 25 \text{ V}, V_{GE} = 0 \text{ V}, f = 1 \text{ MHz}$	8	10	nF	
$C_{oss}$		0.5		nF	
$C_{res}$		0.09		nF	
$Q_g$	$I_C = I_{C90}, V_{GE} = 15 \text{ V}, V_{CE} = 0.5 \cdot V_{CES}$	180		nC	
$Q_{ge}$		45		nC	
$Q_{gc}$		120		nC	
$t_{d(on)}$	Inductive load, $T_J = 125^\circ\text{C}$ $I_C = I_{C90}, V_{GE} = 15 \text{ V}$ $V_{CE} = 600 \text{ V}, R_{on} = 6.8 \Omega, R_{off} = 11 \Omega$ Remarks: Switching times may increase for $V_{CE}$ (Clamp) > 600 V, $T_J > 125^\circ\text{C}$ or increased $R_G$	80		ns	
$t_{rl}$		150		ns	
$t_{d(off)}$		800		ns	
$t_n$		2000		ns	
$E_{on}$		3.2		mJ	
$E_{off}$		-	22	mJ	
$R_{thJC}$			0.31	K/W	
$R_{thCK}$		0.05		K/W	

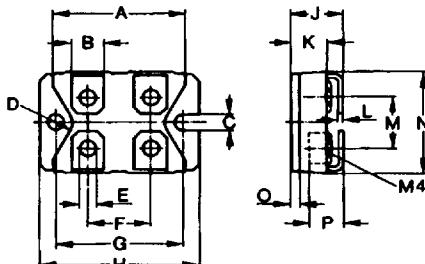
## Reverse Diode (FRED)

Characteristic Values  
( $T_J = 25^\circ\text{C}$ , unless otherwise specified)

min. typ. max.

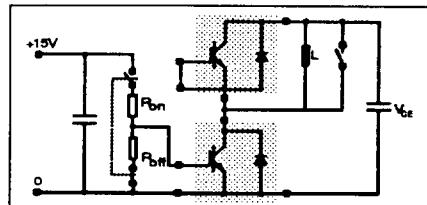
$V_F$	$I_F = I_{C90}, V_{GE} = 0 \text{ V}$ Pulse test, $t \leq 300 \mu\text{s}$ , duty cycle $\delta \leq 2\%$		2.3	V
$I_{RM}$	$I_F = I_{C90}, V_{GE} = 0 \text{ V}, -di_F/dt = 480 \text{ A}/\mu\text{s}, T_J = 125^\circ\text{C}$		66	A
$t_n$	$T_J = 125^\circ\text{C}, V_R = 360 \text{ V}$	150		ns

## Dimensions

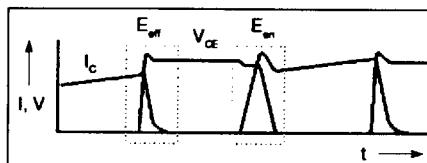


M4 screws (4x) supplied

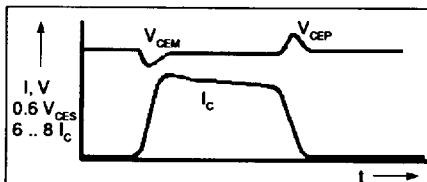
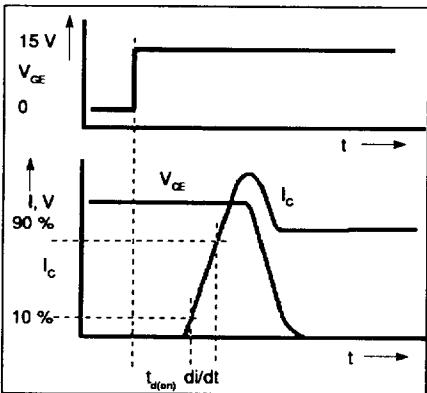
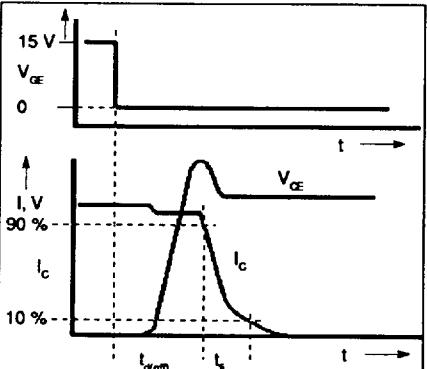
Dim.	Millimeter Min.	Max.	Inches Min.	Max.
A	31.5	31.7	1.241	1.249
B	7.8	8.2	0.307	0.323
C	4.0	-	0.158	-
D	4.1	4.3	0.162	0.169
E	4.1	4.3	0.162	0.169
F	14.9	15.1	0.587	0.595
G	30.1	30.3	1.186	1.193
H	38.0	38.2	1.497	1.505
J	11.8	12.2	0.465	0.481
K	8.9	9.1	0.351	0.359
L	0.75	0.85	0.030	0.033
M	12.6	12.8	0.496	0.504
N	25.2	25.4	0.993	1.001
O	1.95	2.05	0.077	0.081
P	-	5.0	-	0.197



Test circuit for  $E_{on}$ ,  $E_{off}$ , SCSOA and RBSOA  
 $R_{on} = 6.8 \Omega$        $L > 100 \mu\text{H}$   
 $R_{off} = 11 \Omega$  for RBSOA,  $E_{off}$



Typical V/I waveforms for inductive load

SCSOA conditions  $V_{CE} = 600 \text{ V}$ ,  
 $V_{CEM} = 0.5 V_{CES}$ ,  $V_{CEP} < V_{CES}$ ,  $T_J = 125^\circ\text{C}$ Turn-on waveforms  $E_{on}$ Turn-off waveforms  $E_{off}$  RBSOA